## NSN 5961-01-041-6810

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View Online at https://aerobasegroup.com/nsn/5961-01-041-6810 **Inclosure Material:** Metal **Overall Length:** 0.450 inches **Overall Height:** Between 0.250 inches and 0.450 inches Overall Width: 1.050 inches **Overall Diameter:** 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 350.0 breakdown voltage, collector-to-base, emitter open and 300.0 breakdown voltage, collector-to-emitter, base open and 6.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 3.00 amperes source cutoff current and 7.00 amperes source cutoff current **Power Rating Per Characteristic:** 120.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 uninsulated wire lead and 1 case **Specification Data:** 80131-release6555 professional/industrial association specification Shelf Life: N/a

No

**Unit Of Measure:** 

Demilitarization:

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